

Silicon NPN Power Transistors

2SC1624 2SC1625

DESCRIPTION

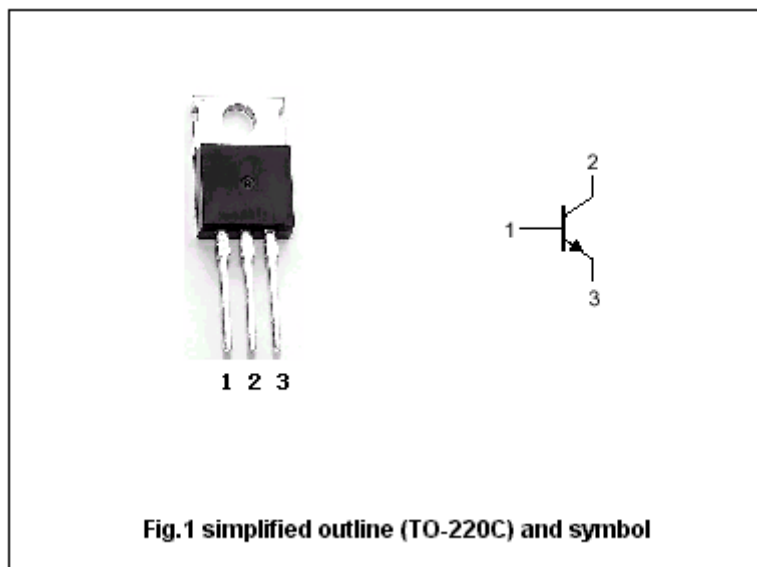
- With TO-220 package
- Complement to type 2SA814/815
- High breakdown voltage

APPLICATIONS

- Medium power amplifier applications
- Driver stage amplifier applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



Absolute maximum ratings (Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SC1624	120	V
		2SC1625	100	
V _{CEO}	Collector-emitter voltage	2SC1624	120	V
		2SC1625	100	
V _{EBO}	Emitter-base voltage	Open collector	5	V
I _C	Collector current		1	A
I _E	Emitter current		-1	A
P _C	Collector power dissipation	T _C =25°C	15	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{(BR)CEO}	Collector-emitter breakdown voltage	2SC1624	I _C =10mA; I _B =0	120			V
		2SC1625		100			
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA; I _C =0	5			V	
V _{CEsat}	Collector-emitter saturation voltage	I _C =500mA; I _B =50mA			0.5	V	
V _{BE}	Base-emitter on voltage	I _C =500mA; V _{CE} =5V			1.0	V	
I _{CBO}	Collector cut-off current	V _{CB} =50V; I _E =0			1.0	μA	
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			1.0	μA	
h _{FE-1}	DC current gain	I _C =150mA; V _{CE} =5V	70		240		
h _{FE-2}	DC current gain	I _C =500mA; V _{CE} =5V	40				
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=1MHz		20		pF	
f _T	Transition frequency	I _C =150mA; V _{CE} =5V		30		MHz	

◆ h_{FE-1} Classifications

O	Y
70-140	120-240

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PACKAGE OUTLINE

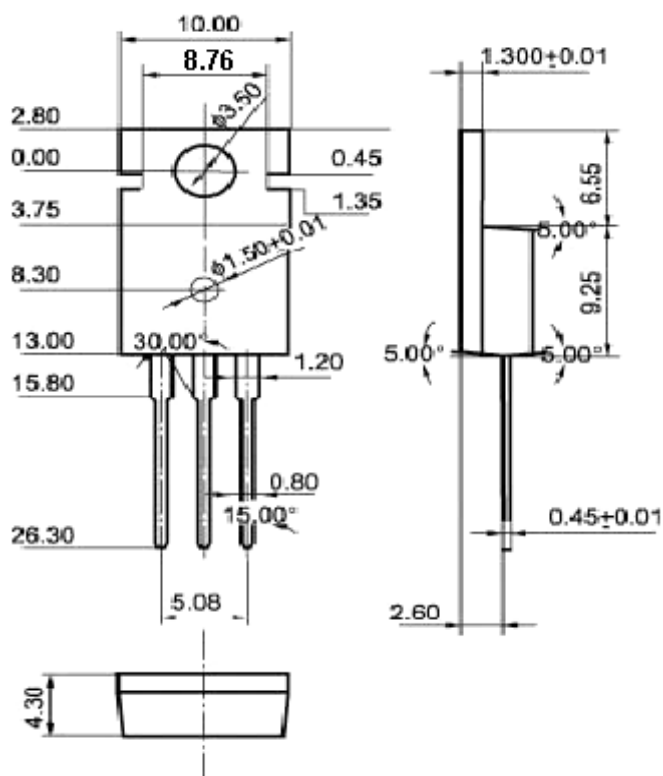


Fig.2 outline dimensions (unindicated tolerance: ± 0.10 mm)